

Talks and Conference Contributions

- [1] F. Demaria, S. Lorch, S. Menzel, M.C. Riedl, F. Rinaldi, R. Rösch, and P. Unger, “Design of highly-efficient high-power optically-pumped semiconductor disk lasers”, *21st IEEE International Semiconductor Laser Conference, ISLC2008*, Sorrento, Italy, Sept. 2008.
- [2] A. Gadallah, A. Kroner, I. Kardosh, F. Rinaldi, and R. Michalzik, “Oblong-shaped VCSELs with pre-defined mode patterns”, *SPIE Photonics Europe, Conf. on Semiconductor Lasers and Laser Dynamics III*, Strasbourg, France, Apr. 2008.
- [3] J. Hertkorn, F. Lipski, P. Brückner, S.B. Thapa, T. Wunderer, F. Scholz, A. Chuvilin, U. Kaiser, M. Beer, and J. Zweck, “Process optimization for the effective reduction of threading dislocations in MOVPE grown GaN using in situ deposited SiN_x”, poster at *14th Int. Conf. on MOVPE (ICMOVPE XIV)*, Metz, France, June 2008.
- [4] A. Kroner, F. Rinaldi, R. Rösch, I. Kardosh, and R. Michalzik, “Towards a compact particle manipulation system based on arrays of vertical-cavity laser diodes”, *Nonlinear Microscopy and Optical Control, NMOC 2008*, Münster, Germany, Feb. 2008.
- [5] A. Kroner, C. Schneck, F. Rinaldi, R. Rösch, and R. Michalzik, “Application of vertical-cavity laser-based optical tweezers for particle manipulation in microfluidic channels”, *SPIE Photonics Europe, Conf. on Nanophotonics*, Strasbourg, France, Apr. 2008.
- [6] A. Kroner, F. Rinaldi, R. Rösch, I. Kardosh, and R. Michalzik, “Ultra-miniaturized optical particle manipulation using densely integrated laser arrays”, *1st Int. l Sympos. on Optical Tweezers in Life Sciences*, Berlin, Germany, May 2008.
- [7] F. Lipski, S.B. Thapa, J. Hertkorn, T. Wunderer, S. Schwaiger, F. Scholz, M. Feneberg, K. Thonke, H. Hochmuth, M. Lorenz, and M. Grundmann, “Studies towards freestanding GaN in hydride vapor phase epitaxy by in-situ etching of a sacrificial ZnO buffer layer”, poster at *5th International Workshop on Nitride Semiconductors (IWN2008)*, Montreux, Switzerland, Oct. 2008.
- [8] R. Michalzik, J.M. Ostermann, and P. Debernardi, “Polarization-stable monolithic VCSELs” (invited), *SPIE Photonics West 2008, Vertical-Cavity Surface-Emitting Lasers XII*, San Jose, CA, USA, Jan. 2008.
- [9] F. Rinaldi, “HRXRD characterization of highly complex MBE grown multilayer structure for optoelectronics applications”, *17th European Heterostructure Technology Workshop, HETECH 2008*, Venice, Italy, Nov. 2008.
- [10] F. Scholz, S.B. Thapa, J. Hertkorn, T. Wunderer, F. Lipski, A. Reiser, Y. Xie, M. Feneberg, K. Thonke, R. Sauer, M. Dürschnabel, L.D. Yao, and D. Gerthsen, “Epitaxial growth of ZnO-GaN Hetero-Nanorods and GaN Nanotubes”, *3rd Nanowire Growth Workshop*, Duisburg, Germany, Sept. 2008.

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- [11] F. Scholz, “Epitaxial growth of high quality GaN and AlN by MOVPE”, *Workshop “Quantum cascade lasers: Intersubband transitions–physics and technology”*, University of Göteborg, Sweden, Oct. 2008.
- [12] F. Scholz, K. Forghani, F. Lipski, S. Schwaiger, S.B. Thapa, T. Wunderer, R.A.R. Leute, I. Tischer, M. Feneberg, K. Thonke, O. Klein, and U. Kaiser, “Untersuchungen zur MOVPE von AlGaIn direkt auf Saphir”, *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [13] F. Scholz, F. Lipski, P. Brückner, S. Schwaiger, J. Hertkorn, and T. Wunderer, “Hydrid-Gasphasenepitaxie von GaN: Der Weg zum GaN-Substrat?”, *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [14] S. Schwaiger, F. Lipski, T. Wunderer, and F. Scholz, “Wachstum unpolarer a-orientierter GaN-Schichten mittels MOVPE”, *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [15] S.B. Thapa, J. Hertkorn, F. Scholz, G.M. Prinz, M. Feneberg, M. Schirra, K. Thonke, R. Sauer, O. Klein, J. Biskupek, and U. Kaiser, “Growth and studies of Si doped AlN layer”, *14th Int. Conf. on MOVPE (ICMOVPE XIV)*, Metz, France, June 2008.
- [16] S.B. Thapa, J. Hertkorn, T. Wunderer, F. Scholz, A. Reiser, G.M. Prinz, M. Schirra, K. Thonke, and R. Sauer, “MOVPE growth of GaN around ZnO nanopillars”, poster at *14th Int. Conf. on MOVPE (ICMOVPE XIV)*, Metz, France, June 2008.
- [17] T. Wunderer, J. Hertkorn, F. Lipski, P. Brückner, F. Scholz, M. Feneberg, M. Schirra, K. Thonke, A. Chuvilin, and U. Kaiser, “Bluish-green semipolar GaInN/GaN light emitting diode on $\{1\bar{1}01\}$ GaN side facets”, *SPIE Photonics West*, San Jose, USA, Jan. 2008.
- [18] T. Wunderer, J. Hertkorn, F. Lipski, P. Brückner, M. Feneberg, M. Schirra, K. Thonke, I. Knoke, E. Meissner, A. Chuvilin, U. Kaiser, and F. Scholz, “Semipolar GaInN/GaN LEDs on $\{1\bar{1}01\}$ GaN side facets”, *Philips Lumileds*, San Jose, CA, USA, Jan. 2008.
- [19] T. Wunderer, J. Hertkorn, F. Lipski, P. Brückner, M. Feneberg, M. Schirra, K. Thonke, I. Knoke, E. Meissner, A. Chuvilin, U. Kaiser, and F. Scholz, “Semipolar GaInN/GaN LEDs on $\{1\bar{1}01\}$ GaN side facets”, *USCB*, Santa Barbara, CA, USA, Feb. 2008.
- [20] T. Wunderer, F. Lipski, J. Hertkorn, P. Brückner, F. Scholz, M. Feneberg, R. Sauer, and K. Thonke, “Semipolar $\{1\bar{1}01\}$ GaInN quantum wells for green light emitting diodes”, *DPG-Tagung*, Berlin, Germany, Feb. 2008.
- [21] T. Wunderer, F. Lipski, J. Hertkorn, S. Schwaiger, and F. Scholz, “Fabrication of 3D InGaIn/GaN structures providing semipolar GaN planes for efficient green light emission”, *5th International Workshop on Nitride Semiconductors (IWN2008)*, Montreux, Switzerland, Oct. 2008.

- [22] T. Wunderer, F. Lipski, S. Schwaiger, J. Hertkorn, F. Scholz, M. Wiedenmann, M. Feneberg, and K. Thonke, "Herstellung von 3D GaInN/GaN Strukturen mit semipolaren Oberflächen für effiziente grüne Licht-Emission", *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [23] T. Wunderer, M. Fikry, J. Hertkorn, S. Schwaiger, F. Lipski, and F. Scholz, "Einfluss der Mg-Dotierung nahe der aktiven Zone auf die Effizienz von GaN-basierten LEDs und Lasern", *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [24] P. Debernardi, A. Kroner, F. Rinaldi, and R. Michalzik, "Hot-cavity model for non-circular VCSELs", *21st IEEE Int.'l Semicond. Laser Conf.*, Sorrento, Italy, Sept. 2008.
- [25] M. Feneberg, T. Wunderer, F. Lipski, P. Brückner, F. Scholz, R. Sauer, and K. Thonke, "Semipolar $\{10\bar{1}1\}$ GaInN quantum wells for green light emitting diodes", *DPG-Tagung*, Berlin, Germany, Feb. 2008.
- [26] O. Klein, J. Biskupek, U. Kaiser, S.B. Thapa, and F. Scholz, "Quantitative dislocation analysis of 2H AlN:Si grown on $\{0001\}$ sapphire", *14th European Microscopy Congress (EMC 2008)*, Aachen, Germany, Sept. 2008.
- [27] A.V. Lobanova, E.V. Yakovlev, R.A. Talalaev, S.B. Thapa, and F. Scholz, "Growth conditions and surface morphology of AlN MOVPE", poster at *14th Int. Conf. on MOVPE (ICMOVPE XIV)*, Metz, France, June 2008.
- [28] T. Malinauskas, K. Jarasiunas, F. Scholz, and P. Brückner, "Diffusion and recombination of degenerate carrier plasma in GaN", poster at *5th International Workshop on Nitride semiconductors (IWN2008)*, Montreux, Switzerland, Oct. 2008.
- [29] S. Metzner, F. Bertram, T. Hempel, J. Christen, T. Wunderer, and F. Scholz, "Hochauflöste Kathodolumineszenzuntersuchungen an grün-emittierenden InGaN QWs auf $\{10\bar{1}1\}$ -GaN-Facetten", *DGKK-Workshop III-V-Epitaxie*, Braunschweig, Germany, Dec. 2008.
- [30] G.M. Prinz, I. Tischer, M. Schirra, M. Feneberg, S.B. Thapa, F. Scholz, Y. Taniyasu, M. Kasu, R. Sauer, and K. Thonke, "Optical investigation of doped and undoped AlN layers", *DPG-Tagung*, Berlin, Germany, Feb. 2008.
- [31] I. Tischer, M. Schirra, M. Feneberg, G.M. Prinz, R. Sauer, K. Thonke, T. Wunderer, J. Hertkorn, F. Lipski, P. Brückner, F. Scholz, A. Chuvilin, U. Kaiser, I. Knoke, and E. Meissner, "Spatial distribution of structural defects in GaN", *DPG-Tagung*, Berlin, Germany, Feb. 2008.